

substrate of aluminum nitride. The material used for the ceramic substrate is not limited to aluminum nitride, indeed other ceramic materials such as carbide ceramics, oxide ceramics, nitride ceramics and the like may also be equally used instead.

Some examples of carbide ceramics include, by way of examples not limitative, silicon carbide, zirconium carbide, titanium carbide, tantalum carbide, tungsten carbide and the like. Some examples of oxide ceramics include, by way of examples not limitative, alumina, zirconia, cordierite, mullite and the like. Some examples of nitride ceramics include, by way of examples not limitative, other than the aluminum nitride as described above, silicon nitride, boron nitride, titanium nitride and the like.

Among these ceramic materials, in general, nitride ceramics, and carbide ceramics are preferred to oxide ceramics because of their thermal conductivity. The sintered bodies may be of single material or of a plurality of materials.

IN THE CLAIMS:

Please cancel claims 11-28 without prejudice to or disclaimer of the subject matter contained therein.

Please add new claims 29-40 as follows:

29. A ceramic heater for heating a wafer, comprising a disk-shaped ceramic substrate and a heat generation pattern formed in an interior of the ceramic substrate; a part of the heat generation pattern being displaced on an offset level different from others of said heat generation pattern in a thickness direction of said ceramic substrate; and a maximum amount of offset displacement in said heat generation pattern being in a range of 5 to 2000 μm .--

--30. A ceramic heater according to claim 29, wherein said heat generation pattern is flat at a cross-section in the thickness direction of said ceramic substrate.--

--31. A ceramic heater according to claim 29, wherein said heat generation pattern comprises spiral wire bodies.--

--32. A ceramic heater according to claim 29, wherein an amount of offset displacement between mutually adjacent portions in said heat generation patterns is in a range of 1 to 100 μm .--

--33. A ceramic heater according to claim 29, wherein said maximum amount of offset displacement is in a range of 3 to 500 μm .--

--34. A ceramic heater according to claim 29, wherein said maximum amount of offset displacement is in a range of 40 to 500 μm .--

--35. A ceramic heater according to claim 29, wherein said ceramic substrate is made of a nitride ceramic or a carbide ceramic.--

--36. A ceramic heater according to claim 29, wherein said ceramic substrate has an anti-thermal shock property ΔT of 190 to 200°C.--

--37. A ceramic heater according to claim 29, wherein said heat generation pattern is flat at a cross-section in the thickness direction of said ceramic substrate and has a thickness of 5 to 50 μm .--

--38. A ceramic heater according to claim 29, wherein said heat generation pattern comprises spiral wire bodies each having a thickness of 0.1 to 2 mm.--

--39. A ceramic heater according to claim 29, wherein said heat generation pattern comprises spiral wire bodies each having a width of 1 to 10 mm.--

--40. A ceramic heater according to claim 29, wherein said heat generation pattern comprises spiral wire bodies each having an aspect ratio (width/thickness) of 1 to 10.--

REMARKS

Claims 29-40 are pending. By this Amendment, claims 11-28 are canceled. New claims 29-40 replace claims 11-28. Figures 1-3, 5, 7-11 and 13 are amended with proper